

2SJ545

Silicon P Channel MOS FET

REJ03G0892-0400

Rev.4.00

Jun 05, 2006

Description

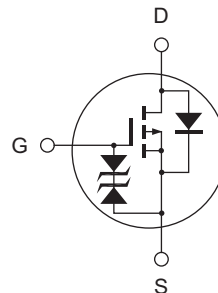
High speed power switching

Features

- Low on-resistance
 $R_{DS(on)} = 0.11 \Omega$ typ.
- Low drive current
- 4 V gate drive devices
- High speed switching

Outline

RENESAS Package code: PRSS0003AE-A
(Package name: TO-220C*FM)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	-60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	-12	A
Drain peak current	I _{D (pulse)} ^{Note 1}	-48	A
Body to drain diode reverse drain current	I _{DR}	-12	A
Avalanche current	I _{AP} ^{Note 3}	-12	A
Avalanche energy	E _{AR} ^{Note 3}	12	mJ
Channel dissipation	P _{ch} ^{Note 2}	25	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

- Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
 2. Value at T_c = 25°C
 3. Value at T_{ch} = 25°C, R_g ≥ 50 Ω

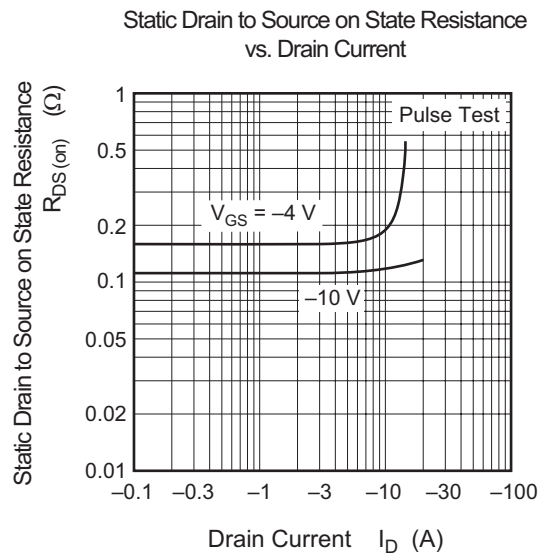
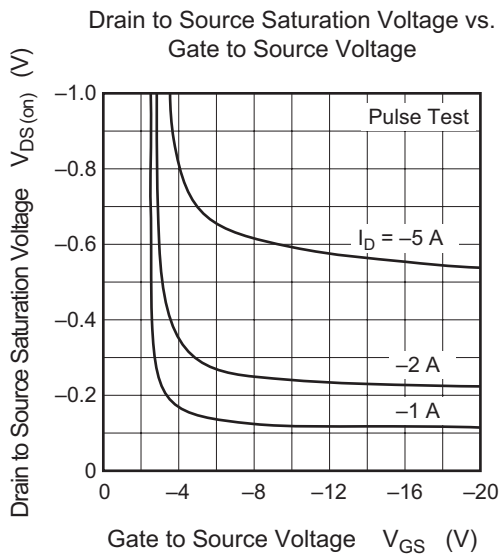
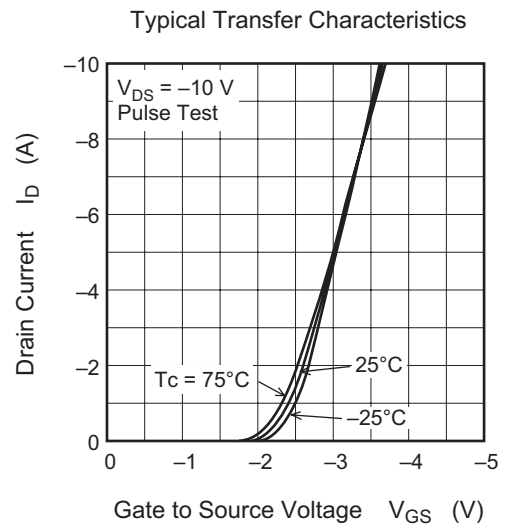
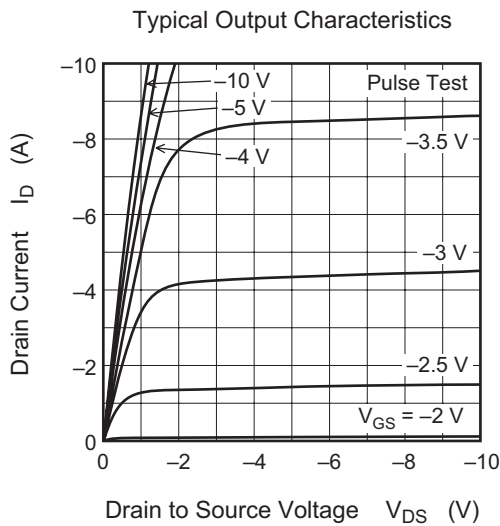
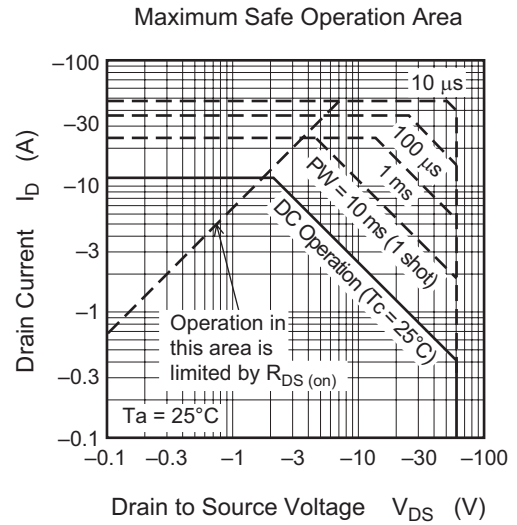
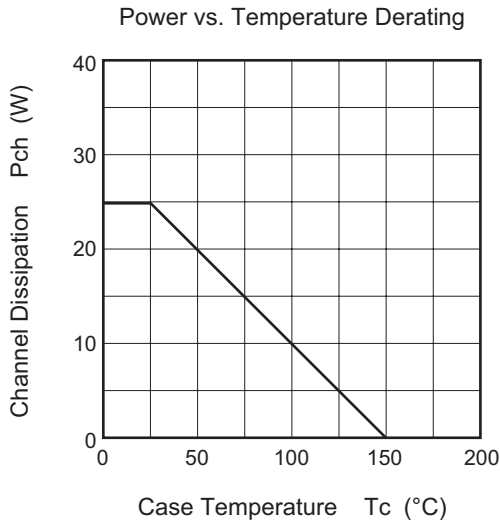
Electrical Characteristics

(Ta = 25°C)

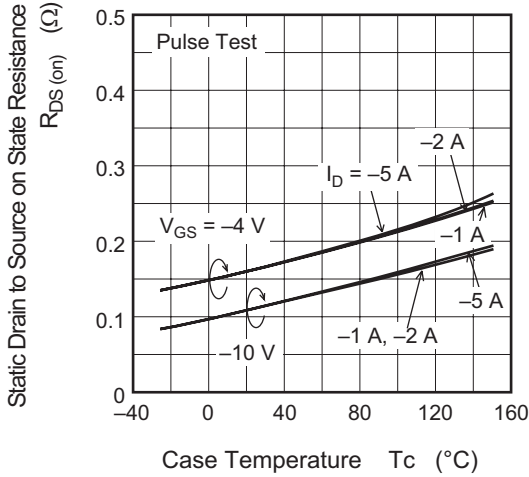
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	-60	—	—	V	I _D = -10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	-10	μA	V _{DS} = -60 V, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Gate to source cutoff voltage	V _{GS (off)}	-1.0	—	-2.0	V	I _D = -1 mA, V _{DS} = -10 V
Static drain to source on state resistance	R _{DS (on)}	—	0.11	0.15	Ω	I _D = -6 A, V _{GS} = -10 V ^{Note 4}
	R _{DS (on)}	—	0.16	0.23	Ω	I _D = -6 A, V _{GS} = -4 V ^{Note 4}
Forward transfer admittance	y _{fs}	5	8	—	S	I _D = -6 A, V _{DS} = -10 V ^{Note 4}
Input capacitance	C _{iss}	—	580	—	pF	V _{DS} = -10 V
Output capacitance	C _{oss}	—	300	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	85	—	pF	f = 1 MHz
Turn-on delay time	t _{d (on)}	—	10	—	ns	V _{GS} = -10 V
Rise time	t _r	—	55	—	ns	I _D = -6 A
Turn-off delay time	t _{d (off)}	—	85	—	ns	R _L = 6 Ω
Fall time	t _f	—	60	—	ns	
Body to drain diode forward voltage	V _{DF}	—	-1.2	—	V	I _F = -12 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	60	—	ns	I _F = -12 A, V _{GS} = 0 di _F /dt = 50 A/μs

- Note: 4. Pulse test

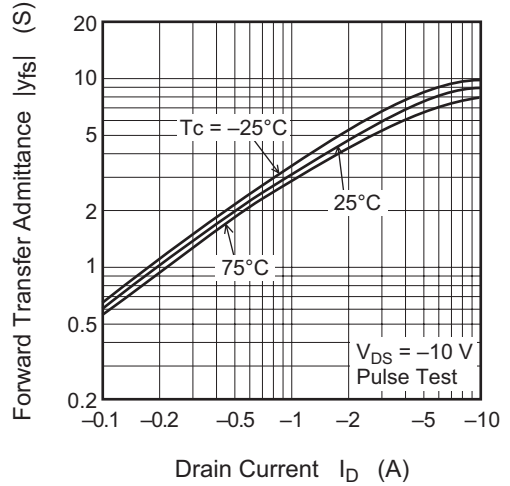
Main Characteristics



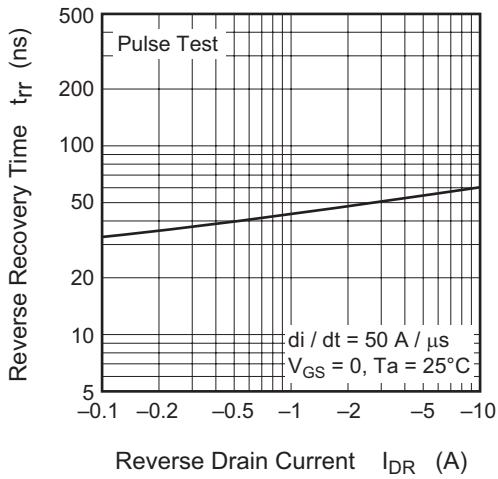
Static Drain to Source on State Resistance vs. Temperature



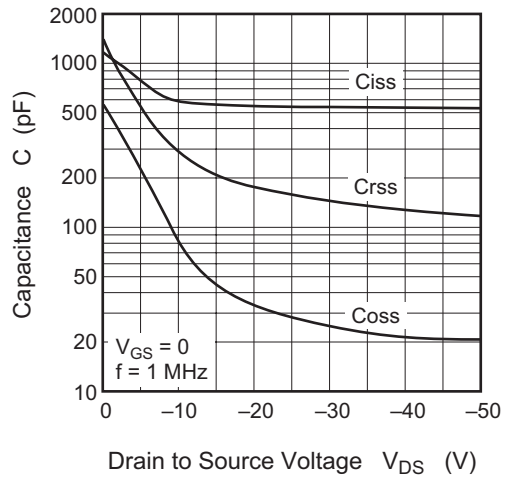
Forward Transfer Admittance vs. Drain Current



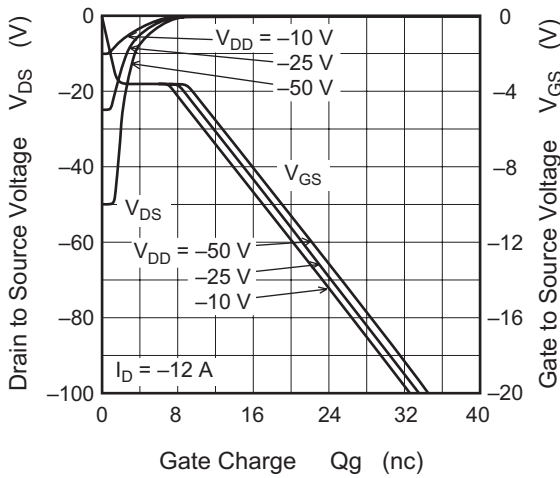
Body-Drain Diode Reverse Recovery Time



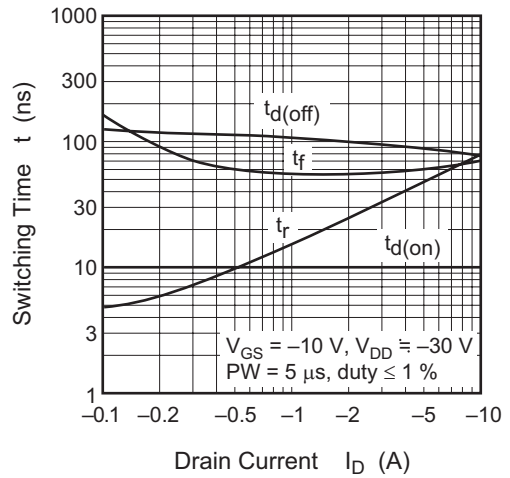
Typical Capacitance vs. Drain to Source Voltage

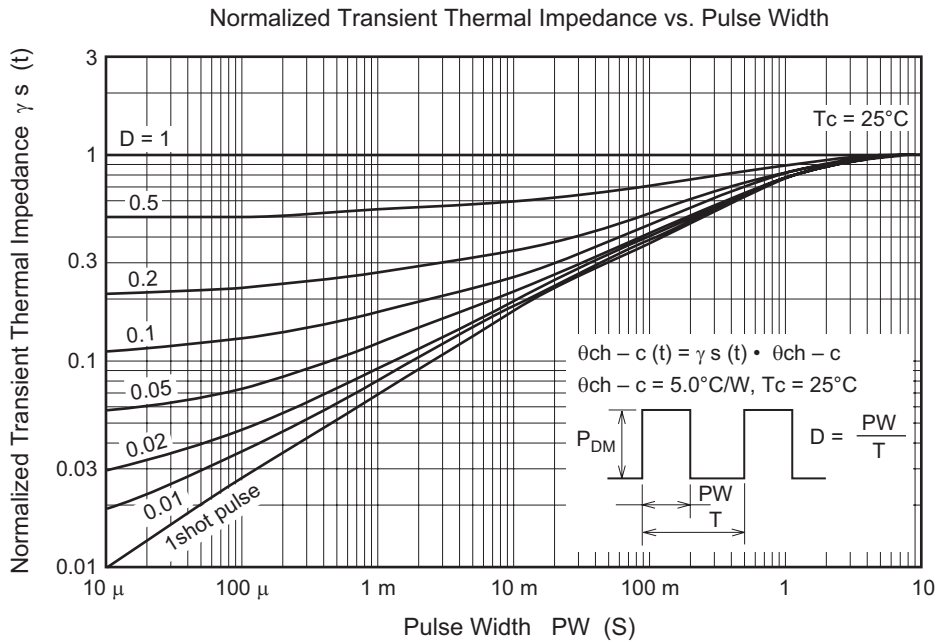
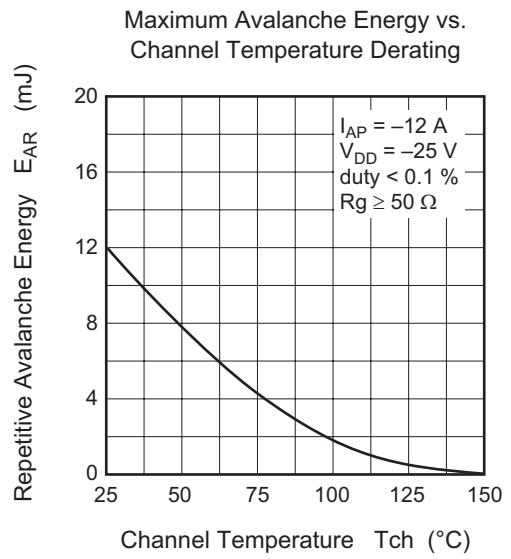
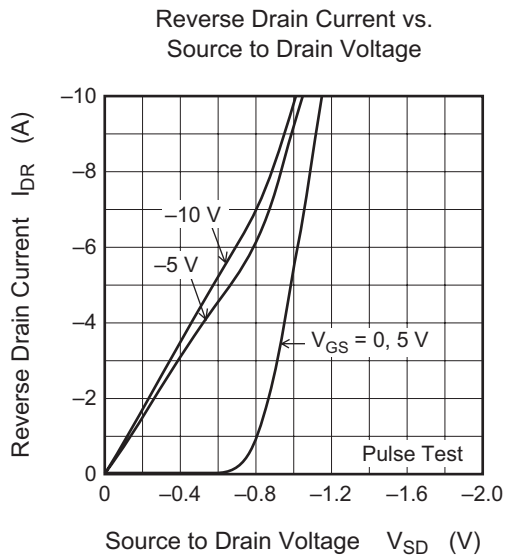


Dynamic Input Characteristics

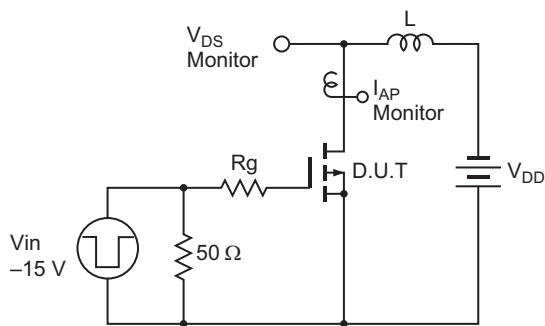


Switching Characteristics



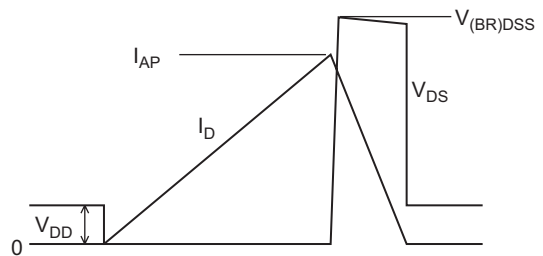


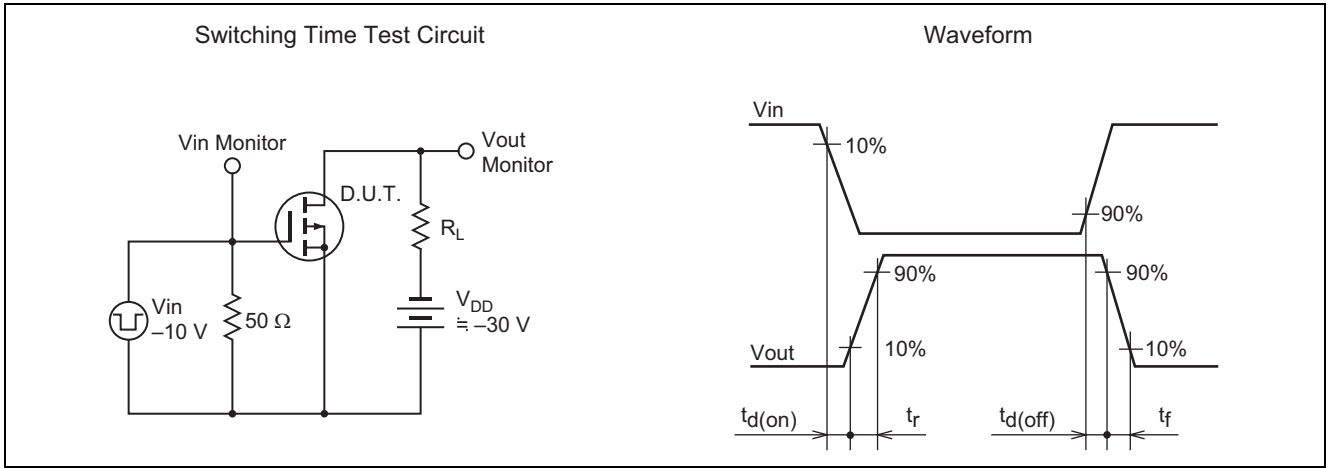
Avalanche Test Circuit



Avalanche Waveform

$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$





Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]	Unit: mm
TO-220CFM	—	PRSS0003AE-A	TO-220CFM / TO-220CFMV	1.9g	

The technical drawing illustrates the TO-220CFM package with the following dimensions:

- Top View:** Width is 10.0 ± 0.3 mm. The distance between the two mounting holes is 3.2 ± 0.2 mm. The diameter of each hole is $\phi 3.2 \pm 0.2$ mm.
- Side View (Left):** Total height is 12.0 ± 0.3 mm. The distance from the top edge to the start of the leads is 1.0 ± 0.2 mm. The lead thickness is 1.15 ± 0.2 mm. The lead height is 0.6 ± 0.1 mm. The distance from the top edge to the bottom of the leads is 4.1 ± 0.3 mm. The lead pitch is 2.54 mm.
- Side View (Right):** Total height is 15.0 ± 0.3 mm. The distance from the top edge to the start of the leads is 4.5 ± 0.3 mm. The lead height is 2.7 ± 0.2 mm. The distance from the top edge to the bottom of the leads is 13.6 ± 1.0 mm. The lead pitch is 2.5 ± 0.2 mm. The lead thickness is 0.7 ± 0.1 mm.

Ordering Information

Part Name	Quantity	Shipping Container
2SJ545-E	600 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.

Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120
Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510